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CLAIMS

	What is claimed is:
1 2	1. (currently amended) A method for fabricating a write pole tip for perpendicular recording, comprising:
3	A) fabricating a P1 <u>write</u> pole, coils and a P2 flux shaping layer;
4	B) depositing a P3 layer on said P2 flux shaping layer;
5	C) depositing a CMP stop layer on said P3 layer;
6	D) depositing at least one sacrificial layer on said CMP stop layer;
7	E) shaping said P3 layer into P3 pole tip;
8	F) removing said at least one sacrificial layer to leave said P3 pole tip; and
9	G) encapsulating said P3 pole tip in a protective layer.
1 2	2. (original) The method of claim 1, wherein: said P3 layer material of B) is a material chosen from the group consisting of
3	CoFe, CoFeN, NiFe, CoFe alloys, CoFeN alloys, NiFe alloys, Cr, Al ₂ O ₃ , and Ru.
1 2	3. (original) The method of claim 1, wherein: said CMP stop layer material of C) is a material chosen from the group consisting
3 4	of Al ₂ O ₃ , Ta ₂ O ₅ , SiO _x N _y , Al ₂ O ₃ alloys, Ta ₂ O ₅ alloys, SiO _x N _y alloys and insulation materials.
1 2 3 4	4. (original) The method of claim 1, wherein: said at least one sacrificial layer of D) comprises a sacrificial layer PS of sacrificial material chosen from the group consisting of NiFe, NiP and plated materials with high ion milling resistances.
1 2 3	5.(original) The method of claim 4, wherein: said at least one sacrificial layer of D) further comprises a seed layer of sacrificial material.
1 2 3	6. (previously presented) The method of claim 5, wherein: said at least one sacrificial layer is formed by creating a cavity surrounded by photo-resist material, said cavity then being filled with sacrificial material.
1 2	7. (original) The method of claim 1, wherein: said shaping of said P3 layer of E) is done by ion milling.
1	8 (previously presented) The method of claim 7 wherein:

said ion milling is done to first produce a straight-sided structure, as said at least

one sacrificial layer masks said P3 pole tip, and then said CMP stop layer acts as a

secondary mask as ion milling is used to bevel the sides of said P3 pole tip.

2 3	said beveled sides of said P3 pole tip are beveled to an angle with the range of 8 degrees to 15 degrees.
1 2	10. (original) The method of claim 1, wherein: said finished P3 pole tip has a width less than 200 nm.
1 2 3	11. (withdrawn) The method of claim 1, wherein: said removing of said at least one sacrificial layer of F) further comprises removing said CMP stop layer.
1 2 3	12. (withdrawn) The method of claim 11, wherein: said removing of said CMP stop layer comprises using Chemical Mechanical Polishing.
1 2 3 4	13. (original) The method of claim 1, wherein: said encapsulating material of G) comprises material matching that of said CMF stop layer.
1 2 3 4	14. (withdrawn) The method of claim 1, wherein: said at least one sacrificial layer of D) comprises magnetic material; and said removing said at least one sacrificial layer of F) requires that all of said magnetic material of said at least one sacrificial layer be completely removed